

**Amendments To The Claims**

1-7.(cancelled)

8.(original) A process for manufacturing a BiMOS microcircuit, comprising:  
forming a buried layer of a first semiconductor material;  
forming a gate oxide for at least one MOS transistor;  
forming a poly-Si layer on the gate oxide;  
forming a base of a second semiconductor material;  
forming a source and a drain for the MOS transistor of a third semiconductor material; and  
forming an emitter of a group III/VI semiconductor on the base.

9.(original) The process of claim 8, further comprising:  
after forming the buried layer, isolating the buried layer into pockets.

10.(original) The process of claim 8, further comprising forming a deep N+ collector.

11.(original) The process of claim 8, further comprising:  
utilizing part of the buried layer as a collector; and  
forming contacts to the base, emitter, collector, source, drain, and poly-Si layer on the gate oxide.

12.(original) The process of claim 8, further comprising forming wells of the second semiconductor material in the buried layer.

13.(original) A BiMOS microcircuit produced according to the process of claim 8.

14-15.(cancelled)

16.(original) A process for manufacturing a heterojunction bipolar transistor (HBT), comprising:

- forming a collector of a first semiconductor;
- forming a base of a second semiconductor;
- forming an emitter of a group III/VI semiconductor;

17.(original) A heterojunction bipolar transistor (HBT) manufactured according to the process of claim 16.

18.(original) The HBT according to claim 17, wherein the group III/VI semiconductor is selected from the group consisting of GaS, GaSe, GaTe, InS, InSe, InTe, and TIS.

19-21.(cancelled)